RHFL4913XX25, RHFL4913XX33, RHFL4913XX50

Rad-hard positive fixed voltage regulator

FLAT-16

SMD5C:
5-connection SMD

TO-257

Features

- 2 and 3 A low dropout voltage
- Embedded overtemperature and overcurrent protection
- Adjustable current limitation
- Output overload monitoring/signalling
- Fixed 2.5 V, 3.3 V, 5.0 V output voltages
- Inhibit (ON/OFF) TTL-compatible control
- Programmable output short-circuit current
- Remote sensing operation
- Rad-hard: tested up to 300 krad Mil Std 883E Method 1019.6 low dose rate conditions
- Heavy Ion, SEL immune

Description

The RHFL4913XX25, RHFL4913XX33 and RHFL4913XX50 belong to a high-performance Rad-hard positive fixed voltage regulator family. Available in various hermetic ceramic packages, they are suitable for harsh environments. Input supply range is up to 12 V. These devices are QML-V qualified, DSCC SMD are 5962F02534 / 02535 / 02536.

Maturity status link
RHFL4913XX25, RHFL4913XX33 and RHFL4913XX50

DS3260 - Rev 14 - May 2019
For further information contact your local STMicroelectronics sales office.

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1 Diagram
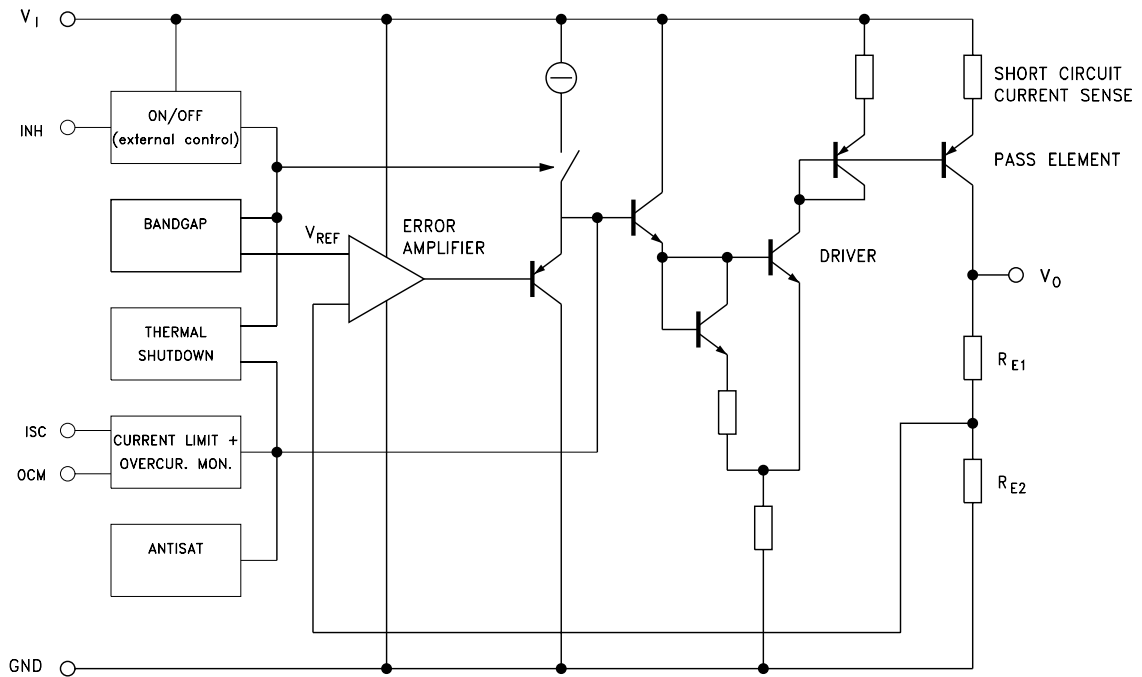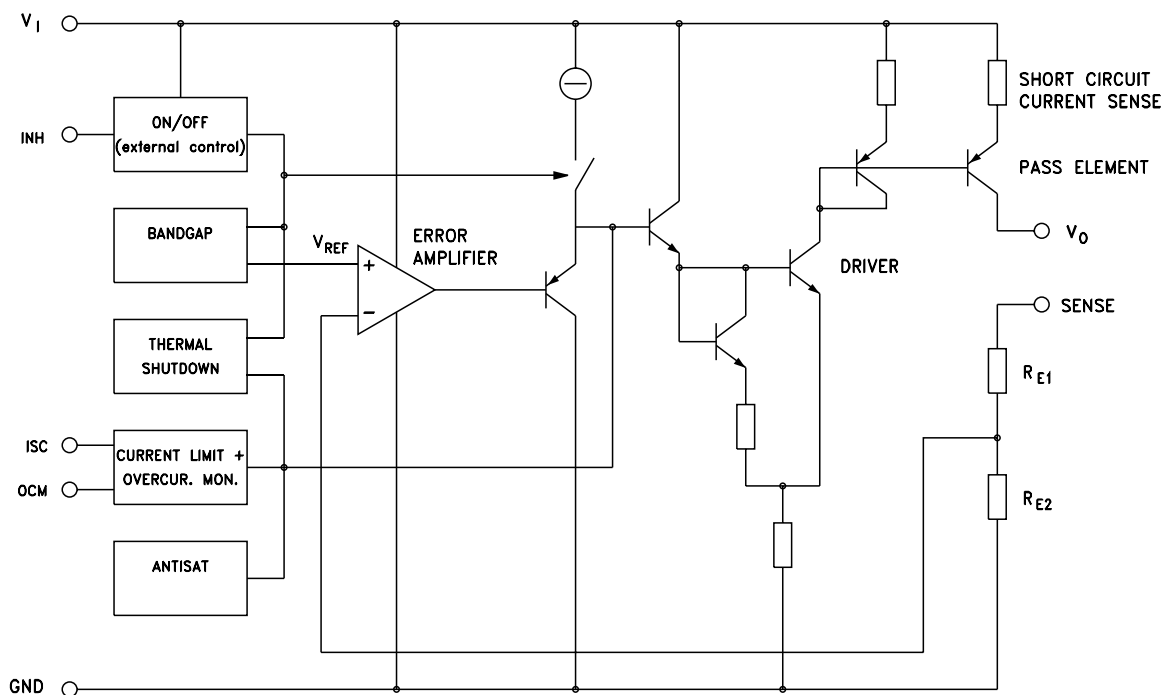
Figure 1. Block diagram for package SMD.5 and TO-257

Figure 2. Block diagram for package Flat-16

2 Pin configuration

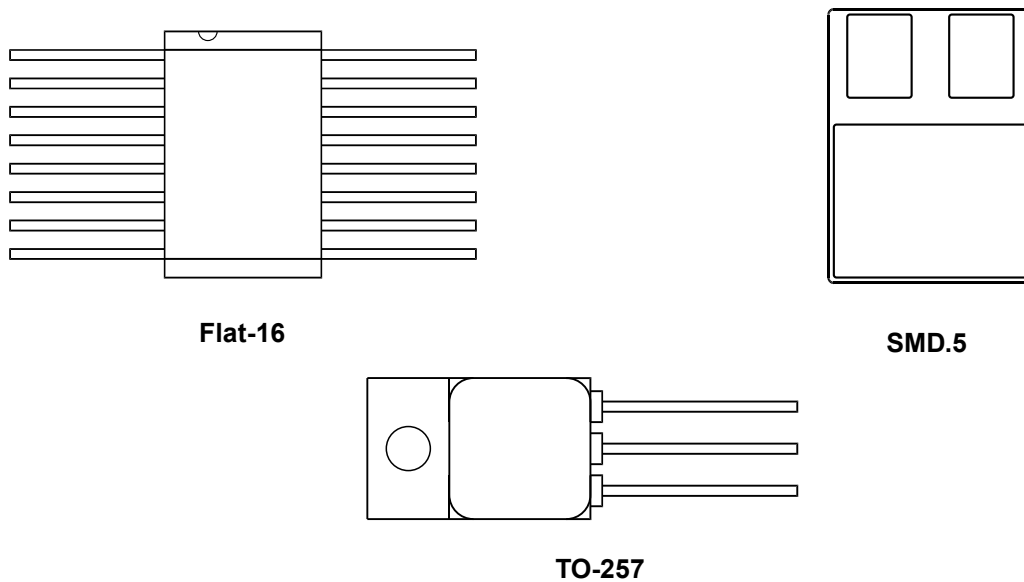Figure 3. **Pin configuration (top view for Flat-16, bottom view for SMD5C)**

Flat-16

SMD.5

TO-257

Table 1. **Pin description**

Pin name	Flat-16 [1]	SMD5C [2]	TO-257
V_O	1, 2, 6, 7	1	3
V_I	3, 4, 5	2	1
GND	13	3	2
I_{SC}	8		
OCM	10		
INHIBIT	14		
SENSE	16		
NC	9, 11, 12, 15		

1. The upper metallic package lid and the bottom metallization are neither connected to regulator die nor to package terminals, hence electrically floating.

2. The upper metallic package lid is neither connected to regulator die nor to package terminals, hence electrically floating.

3   Maximum ratings

Table 2. Recommended maximum operating ratings

Symbol	Parameter	Value	Unit
V_I	DC input voltage, V_I - V_{GROUND}	14	V
I_O	Output current (RHFL4913S, ESY)	3	A
	Output current (RHFL4913KP)	2	
P_D	T_C = 25 °C power dissipation (KP, S version)	15	W
	T_C = 25 °C power dissipation (ESY version)	10	
T_{STG}	Storage temperature range	-65 to +150	°C
T_{OP}	Operating junction temperature range	-55 to +150	°C
T_J	Junction temperature[1]	+150	°C
E_{SD}	Electrostatic discharge capability	Class 3	

1. *Internally limited to about maximum +175 °C by thermal shutdown circuit.*

Note: *Exceeding maximum ratings may damage the device.*

Table 3. Thermal data

Symbol	Parameter	FLAT-16	TO-257	SMD.5	Unit
R_{thJC}	Thermal resistance junction-case max.	8.3	12.5	8.3	°C/W
T_{SOLD}	Maximum soldering temperature, 10 s	300			°C

4 Electrical characteristics

T_J = 25 °C, V_I = V_O + 2.5 V, C_I = C_O = 1 µF, unless otherwise specified.

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_I	Operating input voltage	I_O = 2 A (Flat-16) or 3 A (SMD.5 and TO-257)			12	V
V_O	Output voltage accuracy	V_I = V_O + 2.5 V, I_O = 5 mA	-2		2	%
I_{SHORT}	Output current limit [1]	Adjustable by mask/external resistor		4.5		A
V_O	Operating output voltage	I_O = 2 A, 2.5 V output voltage	2.45		2.55	V
		I_O = 2 A, 3.3 V output voltage	3.23		3.37	
		I_O = 2 A, 5.0 V output voltage	4.9		5.1	
$\Delta V_O/\Delta v_I$	Line regulation	V_I = V_O+2.5 V to 12 V, I_O = 5 mA (+25 °C)			0.3	%
		V_I = V_O+2.5 V to 12 V, I_O = 5 mA (-55 °C)			0.4	
		V_I = V_O+2.5 V to 12 V, I_O = 5 mA (+125 °C)			0.4	
$\Delta V_O/\Delta v_O$	Load regulation	V_I = V_O+2.5 V, I_O = 5 mA to 400 mA (+25 °C)			0.2	%
		V_I = V_O+2.5 V, I_O = 5 mA to 400 mA (-55 °C)			0.3	
		V_I = V_O+2.5 V, I_O = 5 mA to 400 mA (+125 °C)			0.3	
		V_I = V_O+2.5 V, I_O = 5 mA to 1 A (+25 °C)			0.3	
		V_I = V_O+2.5 V, I_O = 5 mA to 1 A (-55 °C)			0.4	
		V_I = V_O+2.5 V, I_O = 5 mA to 1 A (125 °C)			0.4	
Z_{OUT}	Output impedance	I_O = 100 mA DC and 20 mA rms		100		mΩ
I_q	Quiescent current	V_I = V_O + 2.5 V, I_O = 30 mA, ON mode (+25 °C)			8	mA
		V_I = V_O + 2.5 V, I_O = 300 mA, ON mode			25	
		V_I = V_O + 2.5 V, I_O = 1 mA, ON mode			60	
		V_I = V_O + 2.5 V, I_O = 3 A, ON mode (only for SMD.5 and TO-257)			150	
		V_I = V_O+2 V, V_{INH} = 2.4 V, off mode			1	
I_q	Quiescent current	V_I = V_O + 2.5 V, I_O = 1 mA, (T_J = +125 °C, on mode)			40	mA
		V_I = V_O + 2.5 V, I_O = 1 A, (T_J =-55 °C, on mode)			100	

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_d	Dropout voltage	I_O = 400 mA, T_J = -55 °C		300	400	mV
		I_O = 400 mA, T_J = +25 °C		350	450	
		I_O = 400 mA, T_J = +125 °C		450	550	
		I_O = 1 A, T_J = -55 °C			550	
		I_O = 1 A, T_J = +25 °C			650	
		I_O = 1 A, T_J = +125 °C			800	
		I_O = 2 A, T_J = +25 °C		750		
		I_O = 2 A, T_J = +125 °C		950		
$V_{INH(ON)}$	Inhibit voltage	I_O = 5 mA, T_J = -55 to +125 °C			0.8	V
$V_{INH(OFF)}$	Inhibit voltage	I_O = 5 mA, T_J = -55 to +125 °C	2.4			
SVR	Supply voltage rejection [1]	$V_I = V_O$ + 2.5 V ± 1 V, I_O = 5 mA, f = 120 Hz	60	70		dB
		$V_I = V_O$ + 2.5 V ± 1 V, I_O = 5 mA, f = 33 kHz	30	40		
I_{SH}	Shutdown input current	V_{INH} = 5 V		15		µA
V_{OCM}	OCM pin voltage	Sinked I_{OCM} = 24 mA active low		0.38		V
t_{PLH} t_{PHL}	Inhibit propagation delay [1]	$V_I = V_O$ + 2.5 V, V_{INH} = 2.4 V, I_O = 400 mA,	ON-OFF		20	µs
			OFF-ON		100	µs
eN	Output noise voltage [1]	B = 10 Hz to 100 kHz, I_O = 5 mA to 2 A		40		µVrms

1. These values are guaranteed by design. For each application it is strongly recommended to comply with the maximum current limit of the package used.

Figure 4. Application diagram for remote sensing operation
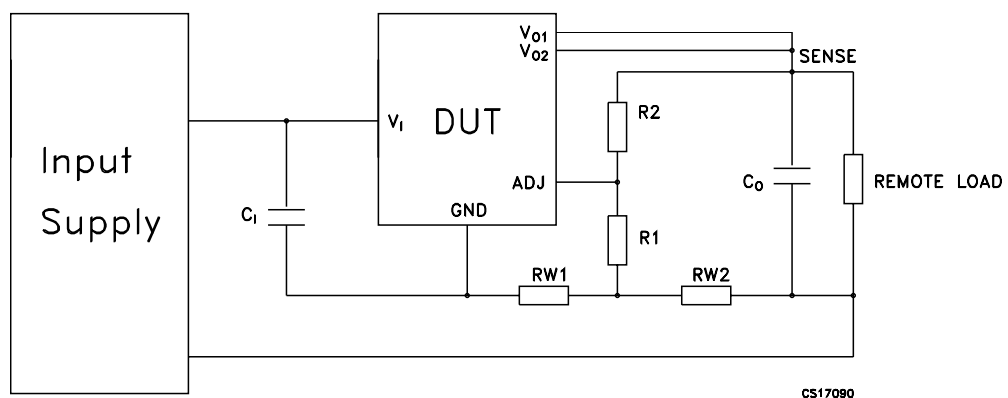
5 Device description

The RHFL4913 fixed voltage contains a PNP type power element controlled by a signal resulting from amplified comparison between the internal temperature compensated band-gap cell and the fraction of the desired output voltage value. This fractional value is obtained from an internal-to-die resistor divider bridge set by STMicroelectronics. The device is protected by several functional blocks.

5.1 Low pin count package limitations

Some functions (INHIBIT, OCM, SENSE) are not available due to lack of pins. Corresponding die pads are by default connected inside silicon.

5.2 SENSE pin

The load voltage is applied by a Kelvin line connected to SENSE pin: Voltage feedback comes from the internal divider resistor bridge. Therefore possible output voltages are set by manufacturer mask metal options. SENSE pin is not available in 3-pin packages.

5.3 Inhibit ON-OFF control

By setting the INHIBIT pin TTL high, the device switches off the output current and voltage. The device is ON when the INHIBIT pin is set low. Since the INHIBIT pin is pulled down internally, it can be left floating in cases where the inhibit function is not used. INHIBIT pin is not available in 3-pin packages.

5.4 Overtemperature protection

A temperature detector internally monitors the power element junction temperature. The device turns off when a temperature of approximately 175 °C is reached, returning to ON mode when back to approximately 40 °C. It should be noted that when the internal temperature detector reaches 175 °C, the active power element can be at 225 °C: the device reliability cannot be guaranteed in case of extensive operation under these conditions.

5.5 Overcurrent protection

I_{SC} pin. An internal non-fold back short-circuit limitation is set with I_{SHORT} > 3.8 A (V_O is 0 V). This value can be reduced by an external resistor connected between I_{SC} pin and V_I pin, with a typical value range of 25 kΩ to 200 kΩ. This adjustment feature is not available in 3-pin packages. To keep excellent V_O regulation, it is necessary to set I_{SHORT} 1.6 times greater than the maximum desired application I_O. When I_O reaches I_{SHORT} – 300 mA, the current limiter overrules regulation and V_O starts to drop and the OCM flag is risen. When no current limitation adjustment is required, I_{SC} pin must be left unbiased (as it is in 3 pin-packages).

5.6 OCM pin

The OCM pin goes low when the current limit becomes active, otherwise $V_{OCM} = V_I$. It is buffered and can sink 10 mA. The OCM pin is internally pulled up by a 5 kΩ resistor. Not available in 3-pin packages.

5.7 Alternate to

The RHFL4913 fixed (and custom) voltages replace all 3-terminal industry devices, providing essential benefits
• Lower dropout
• High radiation performance
• Better SVR
• Saving the high stability external setting resistors

6 Application information

The RHFL4913 fixed voltage is functional as soon as V_I-V_O voltage difference is slightly above the power element saturation voltage. A minimum 0.5 mA I_O ensures perfect "no-load" regulation.

All available V_I pins must always be externally interconnected, same thing for all available V_O pins, otherwise device stability and reliability cannot be granted. All NC pins can be connected to ground. The INHIBIT function switches off the output current in an electronic way, that is very quickly. According to Lenz's law, external circuitry reacts with –LdI/dt terms which can be of high amplitude in case some series-inductance exists. The effect would be a large transient voltage developed on both device terminals. It is necessary to protect the device with Schottky diodes preventing negative voltage excursions. In the worst case, a 14 V Zener diode shall protect the device input.

The device has been designed for high stability and low dropout operation: minimum 1 µF input and output tantalum capacitors are therefore mandatory. Capacitor ESR range is from 0.01 Ω to over 20 Ω. Such range turns out to be useful when ESR increases at low temperature. When large transient currents are expected, larger value capacitors are necessary.

In case of high current operation with expected short-circuit events, caution must be considered relatively to capacitors. They must be connected as close as possible to device terminals. As some tantalum capacitors may permanently fail when submitted to high charge-up surge currents, it is recommended to decouple them with 470 nF polyester capacitors.

Being the RHFL4913 fixed voltage manufactured with very high speed bipolar technology 6 GHz fT transistors), the PCB lay-out must be performed with extreme care, very low inductance, low mutually coupling lines, otherwise high frequency parasitic signals may be picked-up by the device resulting into self-oscillation. User's benefit is a SVR performance extended to far

higher frequencies.

6.1 Remote sensing operation

In case the load is located far from the regulator, it is recommended to comply with the scheme below. To obtain the best regulation, it is in addition essential to care about:

• The wire connecting R2 to the load end must not be crossed by the load current (Kelvin sense)

The noise captured by the wires between the load and the chip could bring a noisy output voltage. In case this happens, it is recommended that shielded cables are used for these connections. The external wrap must be used for connecting the ground of the chip with the load ground. It is also recommended to place 1 µF tantalum capacitors between output and ground close to the device and another next to the load.

7 Notes about Flat-16 package

The bottom of package is metallized to allow user to directly solder the voltage regulator to PCB, no heat sink needed, in order to optimize heat removal performance.

7.1 Radiation performance

The RHFL4913F has been tested against: 300 krad TID ELDERS in accordance with Mil-1019.6, bipolar section: post radiation parameters are within datasheet pre-rad limits.

Submitted to 200 MeV Iodine ions of 60.4 MeV/cm2/mg LET up to 1exp(+7) ions / cm2, no SEL event has been detected.

7.2 Die information

The RHFL4913 fixed is also available in die form. Space dice are electrically tested by STMicroelectronics in such a way that, when mounted in proper thermal and electrical substrate, they provide full compliance with equivalent packaged product.

- Max. die dimensions: 2.794 mm by 3.861 mm or 110 mils by 152 mils
- Die thickness: 357 μm +/- 50 μm
- Pad size: 184 μm by 184 μm
- Metallization: Aluminum 4% silicon alloy
- Die backside: Bare silicon
- Die backside potential: Ground

Figure 5. Die size
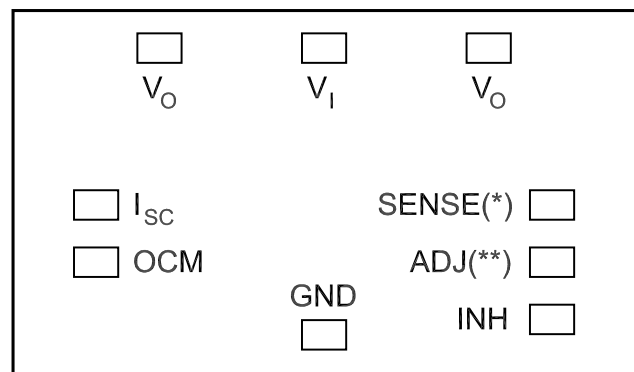
Note: *Die SENSE pad is active in the RHFL4913 fixed die. It shall not be left unbonded. It should be bonded to V_O pin. Die adjust pad is available in the die layout but is not electrically connected to the IC. It shall be left unconnected during hybrid bonding.*

8 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.
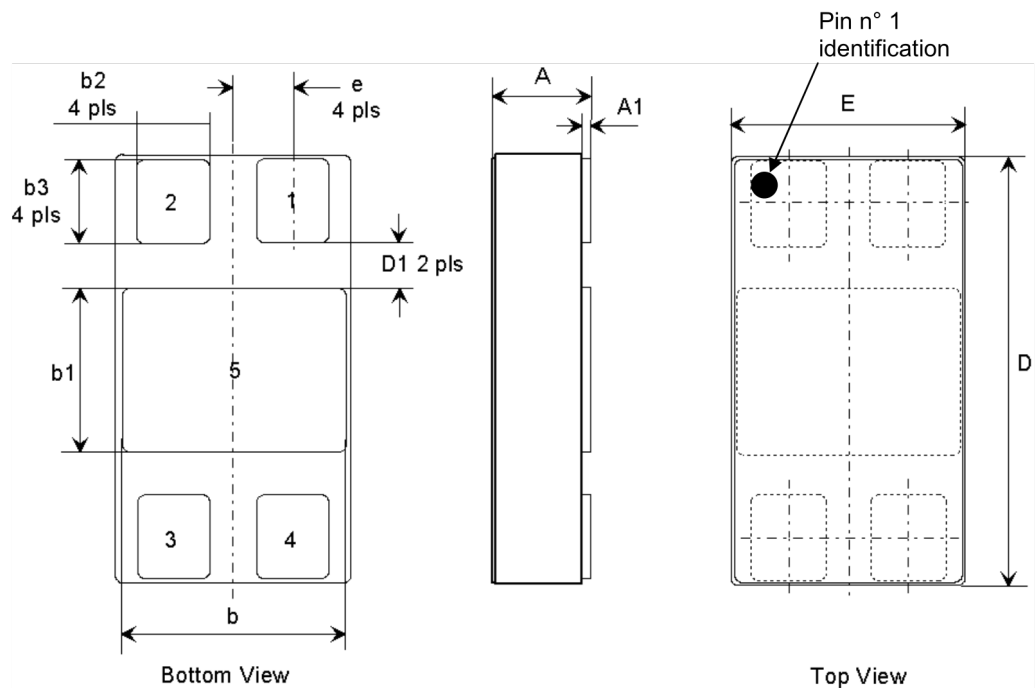
8.1 Flat-16 package information

Figure 6. Flat-16 package outline
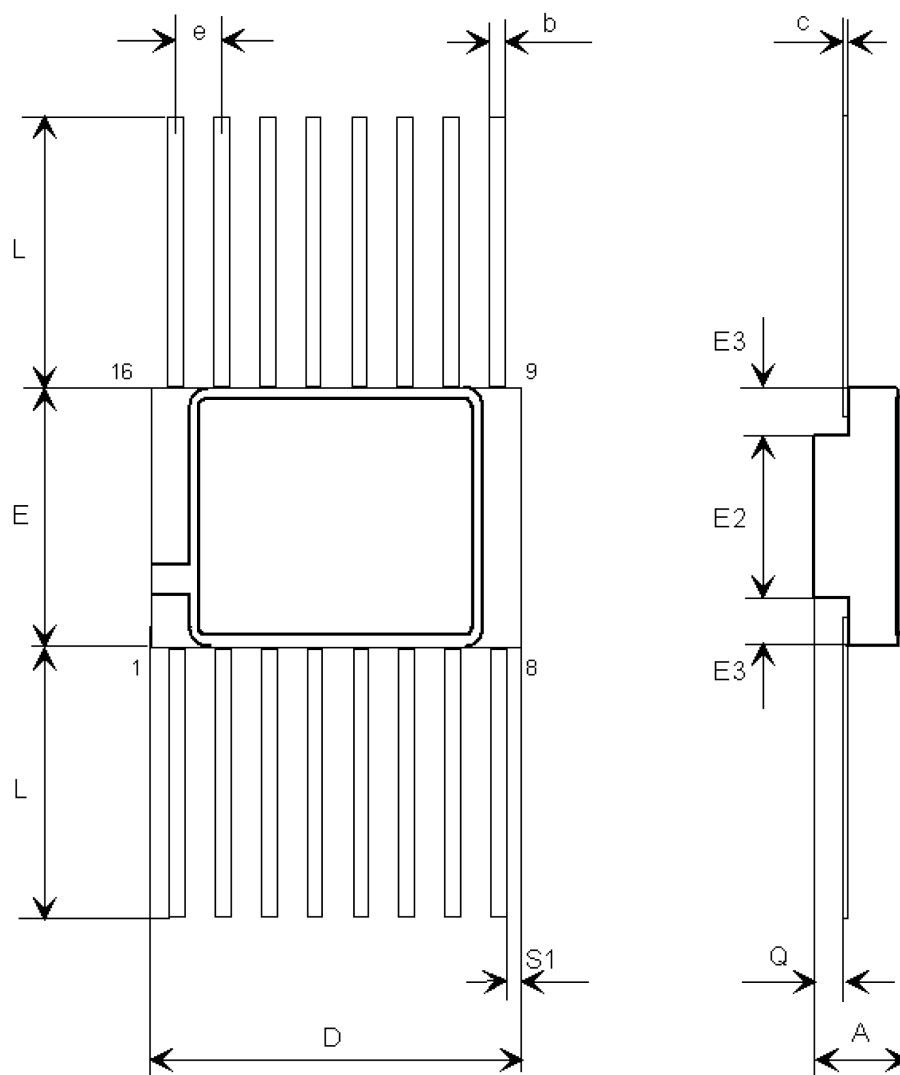

7450901_D

Table 5. **Flat-16 package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.42		2.88
b	0.38		0.48
c	0.10		0.18
D	9.71		10.11
E	6.71		7.11
E2	3.30	3.45	3.60
E3	0.76		
e		1.27	
L	6.35		7.36
Q	0.66		1.14
S1	0.13		

8.2   SMD5C package information

Figure 7. **SMD5C package outline**

7924296_E

Table 6. **SMD5C package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.99	3.15	3.30
A1	0.25	0.38	0.51
b	7.13	7.26	7.39
b1	4.95	5.08	5.21
b2	2.28	2.41	2.54
b3	2.92	3.05	3.18
D	13.71	13.84	13.97
D1	0.76		
E	7.39	7.52	7.65
e		1.91	

8.3 TO-257 package information

Figure 8. TO-257 package outline
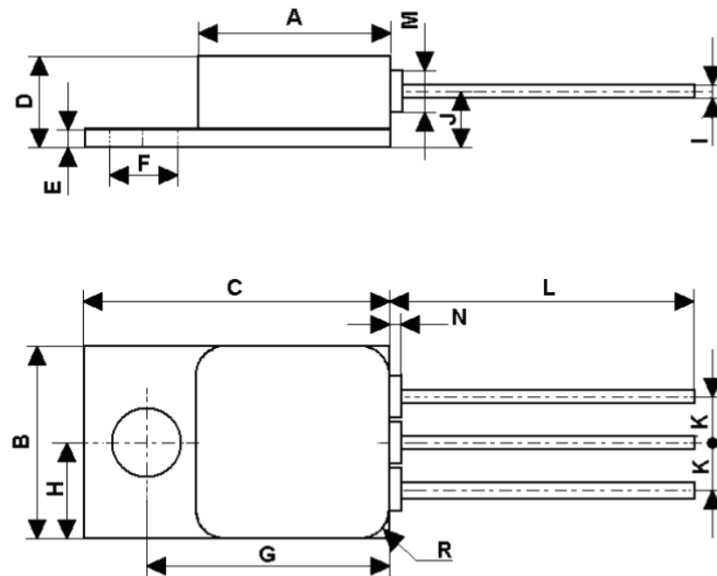
Table 7. TO-257 package mechanical data

Dim.	mm			Inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A		10.54			0.415	
B		10.54			0.415	
C		16.64			0.655	
D	4.7		5.33	0.185		0.210
E		1.02			0.40	
F	3.56	3.68	3.81	0.140	0.145	0.150
G		13.51			0.532	
H		5.26			0.207	
I		0.76			0.030	
J		3.05			0.120	
K		2.54			0.100	
L	15.2		16.5	0.598		0.650
M		2.29			0.090	
N			0.71			0.028
R		1.65			0.065	

9 Ordering information

Table 8. Order codes

Die	Flat-16	SMD.5	TO-257	Terminal finish	VOUT	Quantity level
	RHFL4913KP25-01V	RHFL4913S25-03V	RHFL4913ESY2505V	Gold	2.5 V	QML-V
	RHFL4913KP25-02V	RHFL4913S25-04V	RHFL4913ESY2506V	Solder	2.5 V	QML-V
	RHFL4913KP251	RHFL4913S251	RHFL4913ESY251	Gold	2.5 V	EM1
	RHFL4913KP252	RHFL4913S252	RHFL4913ESY252	Gold	2.5 V	EM1=EM 2+48h B.I.
L491325DIE2V		Flight model		NA	2.5 V	QML-V
L491325DIE2S				NA	2.5 V	EM1
	RHFL4913KP33-01V	RHFL4913S33-03V	RHFL4913ESY3305V	Gold	3.3 V	QML-V
	RHFL4913KP33-02V	RHFL4913S33-04V	RHFL4913ESY3306V	Solder	3.3 V	QML-V
	RHFL4913KP331	RHFL4913S331	RHFL4913ESY331	Gold	3.3 V	EM1
	RHFL4913KP332	RHFL4913S332	RHFL4913ESY332	Gold	3.3 V	EM1=EM 2+48h B.I.
L491333DIE2V				NA	3.3 V	QML-V
L491333DIE2S				NA	3.3 V	EM1
	RHFL4913KP50-01V	RHFL4913S50-03V	RHFL4913ESY5005V	Gold	5.0 V	QML-V
	RHFL4913KP50-02V	RHFL4913S50-04V	RHFL4913ESY5006V	Solder	5.0 V	QML-V
	RHFL4913KP501	RHFL4913S501	RHFL4913ESY501	Gold	5.0 V	EM1
	RHFL4913KP502	RHFL4913S502	RHFL4913ESY502	Gold	5.0 V	EM1=EM 2+48h B.I.
L491350DIE2V				NA	5.0 V	QML-V
L491350DIE2S				NA	5.0 V	EM1

Table 9. Part number-SMD equivalent

ST part number	SMD part number
RHFL4913KP25-01V	5962F0253401VXC
RHFL4913KP25-02V	5962F0253401VXA
RHFL4913KP33-01V	5962F0253501VXC
RHFL4913KP33-02V	5962F0253501VXA
RHFL4913KP50-01V	5962F0253601VXC
RHFL4913KP50-02V	5962F0253601VXA
RHFL4913S25-03V	5962F0253402VYC
RHFL4913S25-04V	5962F0253402VYA
RHFL4913S33-03V	5962F0253502VYC
RHFL4913S33-04V	5962F0253502VYA
RHFL4913S50-03V	5962F0253602VYC
RHFL4913S50-04V	5962F0253602VYA

ST part number	SMD part number
RHFL4913ESY2505V	5962F0253402VZC
RHFL4913ESY2506V	5962F0253402VZA
RHFL4913ESY3305V	5962F0253502VZC
RHFL4913ESY3306V	5962F0253502VZA
RHFL4913ESY5005V	5962F0253602VZC
RHFL4913ESY5006V	5962F0253602VZA
L491325DIE2V	5962F0253402V9A
L491333DIE2V	5962F0253502V9A
L491350DIE2V	5962F0253602V9A

Table 10. Environmental characteristics

Parameters	Conditions	Value	Unit
Output voltage thermal drift	-55 °C to +125 °C	40	ppm/°C
Output voltage radiation drift	From 0 krad to 300 krad at 0.55 rad/s	8	ppm/krad
Output voltage radiation drift	From 0 krad to 300 krad, Mil Std 883E Method 1019.6	6	ppm/krad

Revision history

Table 11. Document revision history

Date	Revision	Changes
05-Oct-2004	4	Mistake in pin description SMD.5 on table 3.
28-Oct-2004	5	New order codes added - tables 4 and 5.
27-May-2005	6	The features, tables 4, 5 and the figures 1, 2 updated.
08-Jun-2005	7	Modified: PD on table 1, the RthJC for TO-257 on table 2 and the tables 6 and 7, added DIE information
26-Aug-2008	8	Added new output 1.5 V, modified: Table 4 on page 6, Table 5 on page 16 and Table 6 on page 17.
02-Oct-2008	9	Modified: Features on page 1, Application information on page 10 and SMD.5 mechanical data on page 14.
20-Nov-2009	10	Modified: Table 5 on page 16.
19-Oct-2010	11	Modified: Section 7 on page 11.
08-Feb-2011	12	Added: note Table 1 on page 4.
07-Dec-2011	13	Removed the note under Table 1 on page 4 and added footnotes 1 and 2.
02-May-2019	14	Updated the description.

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IMPORTANT NOTICE – PLEASE READ CAREFULLY